What is claimed is:

1. In a thin film transistor having a back channel electrode, wherein a voltage of a front channel positioned on the side of a gate wiring of said thin film transistor is made equal to a voltage of said back channel positioned on the side of a back channel electrode by short-circuiting said back channel electrode to a gate electrode through a contact-hole provided in a portion of a semiconductor layer constituting said thin film transistor.

2. A thin film transistor as claimed in claim 1, wherein said back channel electrode is formed of the same material as a material of a pixel electrode connected to one of source and drain electrodes of said thin film transistor.

3. A thin film transistor as claimed in claim 2, wherein said pixel electrode is a transparent electrode.

4. A thin film transistor as claimed in claim 1, wherein said contact-hole is formed in a location remote from an active region of said thin film transistor by at least five microns.

5. A thin film transistor as claimed in claim 1, wherein a passivation film patterned to have a width equal to that of said back channel electrode and said semiconductor layer

are provided between said back channel and said gate insulating film.

6. A thin film transistor as claimed in claim 1, wherein said semiconductor layer patterned to have a width equal to that of said source and drain electrodes of said thin film transistor is provided between said source and drain electrodes and said gate insulating film.

7. A thin film transistor as claimed in claim 1, wherein said semiconductor layer has an ohmic contact layer on the side thereof, which is in contact with said source and drain electrodes.

8. In a fabrication method of a thin film transistor, including the steps of forming a gate electrode wiring pattern and a gate insulating film on a substrate and forming a semiconductor layer and a source and drain electrodes on said gate insulating film, forming a pixel electrode connected to one of said source and drain electrodes and forming a passivation film and a back channel electrode on an active region of said thin film transistor, said fabrication method comprising the steps of patterning said source and drain electrodes without patterning said semiconductor layer, forming said passivation film after the patterning step, patterning a gate contact hole for connecting said back channel

electrode to said gate electrode and an opening portion for said pixel electrode such that said gate contact hole and said opening portion penetrate said passivation film, said semiconductor layer and said gate insulating film, forming an electrically conductive film for said pixel electrode such that said conductive film commonly covers said gate contact hole and said opening portion and patterning said conductive film such that said pixel electrode and said back channel electrode are left as they are, wherein said passivation film and said semiconductor layer, which are left as they are, are patterned simultaneously with using said pixel electrode, said back channel electrode and said source and drain electrodes, which are left as they are as a mask.

9. A fabrication method as claimed in claim 8, wherein said opening portion is provided by removing a portion of the one of said source and drain electrodes, to which said pixel electrode is connected.

10. A fabrication method as claimed in claim 8, wherein said contact hole is formed in a location remote from said active region of said thin film transistor.

11. A fabrication method as claimed in claim 8, wherein a one side of said opening portion is formed such that one side of one of said source and drain electrodes is exposed

through said opening portion and is electrically connected to said pixel electrode.

12. A fabrication method as claimed in claim 8, wherein said semiconductor layer has an ohmic contact layer on the side of said source and drain electrodes and said ohmic contact layer on said active region is patterned simultaneously with the patterning step of said source and drain electrodes.